***flow* PIM 0** | **600 V / 30 A**

Features

- Vincotech clip-in housing
- Trench Fieldstop IGBT's for low saturation losses

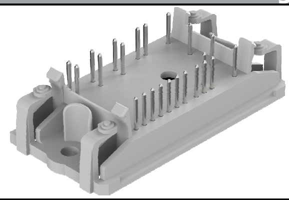
Target Applications

- Industrial Drives
- Embedded Generation

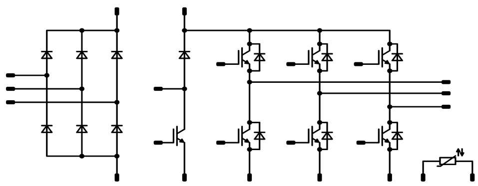
Types

- V23990-P546-A20-PM

flow 0 17mm housing



Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Rectifier Diode				
Repetitive peak reverse voltage	V_{RRM}		1600	V
DC forward current	I_{FAV}	$T_j = T_{jmax}$ T_s = 80 °C	34	A
Surge (non-repetitive) forward current	I_{FSM}	t_p = 10 ms 50 Hz half sine wave T_j = 150 °C	200	A
I^2t-value	I^2t		200	A^2s
Power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	43	W
Maximum Junction Temperature	T_{jmax}		150	°C
Inverter Switch				
Collector-emitter breakdown voltage	V_{CE}		600	V
DC collector current	I_C	$T_j = T_{jmax}$ T_s = 80 °C	31	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	90	A
Turn off safe operating area		V_{CE} ≤ 1200V, T_j ≤ T_{op} max	90	A
Power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	64	W
Gate-emitter peak voltage	V_{GE}		±20	V
Short circuit ratings	t_{SC} V_{CC}	T_j ≤ 150 °C V_{GE} = 15 V	6 360	μs V
Maximum Junction Temperature	T_{jmax}		175	°C

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Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Inverter Diode					
Peak Repetitive Reverse Voltage	V_{RRM}			600	V
DC forward current	I_F	$T_j = T_{jmax}$	T_s = 80 °C	31	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		60	A
Power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	53	W
Maximum Junction Temperature	T_{jmax}			175	°C
Brake Switch					
Collector-emitter breakdown voltage	V_{CE}			600	V
DC collector current	I_C	$T_j = T_{jmax}$	T_s = 80 °C	26	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}		60	A
Turn off safe operating area		V_{CE} ≤ 1200 V, $T_j ≤ T_{op}$ max		60	A
Power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	56	W
Gate-emitter peak voltage	V_{GE}			±20	V
Short circuit ratings	t_{SC} V_{CC}	T_j ≤ 150 °C V_{GE} = 15 V		6 360	µs V
Maximum Junction Temperature	T_{jmax}			175	°C
Brake Diode					
Peak Repetitive Reverse Voltage	V_{RRM}			600	V
DC forward current	I_F	$T_j = T_{jmax}$	T_s = 80 °C	21	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}		40	A
Power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	37	W
Maximum Junction Temperature	T_{jmax}			175	°C
Thermal Properties					
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{op}			-40…+(T_{jmax} - 25)	°C
Isolation Properties					
Isolation voltage	V_{is}	t = 2 s	DC voltage	4000	V
Creepage distance				min 12,7	mm
Clearance				10,07	mm
Comparative tracking index	CTI			>200	

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Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_r [V] V_{CE} [V] V_{DS} [V]	I_C [A] I_F [A] I_D [A]	T_j [°C]	Min	Typ	Max	
Rectifier Diode										
Forward voltage	V_F				30	25 125	0,8	1,20 1,17	1,8	V
Threshold voltage (for power loss calc. only)	V_{to}				30	25 125		0,93 0,80		V
Slope resistance (for power loss calc. only)	r_t				30	25 125		11 15		mΩ
Reverse current	I_r			1600		25			0,05	mA
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,61		K/W
Inverter Switch										
Gate emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,00043	25	5	5,8	6,5	V
Collector-emitter saturation voltage	V_{CEsat}		15		30	25 150	1,1	1,67 1,90	1,9	V
Collector-emitter cut-off current incl. Diode	I_{CES}		0	600		25			0,0016	mA
Gate-emitter leakage current	I_{GES}		20	0		25			300	nA
Integrated Gate resistor	R_{gint}							none		Ω
Turn-on delay time	$t_{d(on)}$	R_{goff} = 4 Ω R_{gon} = 8 Ω	15	300	30	25 150		17 18		ns
Rise time	t_r					25 150		16 18		
Turn-off delay time	$t_{d(off)}$					25 150		156 172		
Fall time	t_f					25 150		88 101		
Turn-on energy loss	E_{on}					25 150		0,52 0,71		mWs
Turn-off energy loss	E_{off}					25 150		0,72 0,90		
Input capacitance	C_{ies}	f = 1 MHz	0	25		25		1630		pF
Output capacitance	C_{oss}							108		
Reverse transfer capacitance	C_{rss}							50		
Gate charge	Q_G		±15	480	30	25		167		nC
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,49		K/W
Inverter Diode										
Diode forward voltage	V_F				30	25 150	1,25	1,64 1,66	1,95	V
Peak reverse recovery current	I_{RRM}	R_{gon} = 8 Ω	15	300	30	25 150		25 28		A
Reverse recovery time	t_{rr}					25 150		176 256		ns
Reverse recovered charge	Q_{rr}					25 150		1,36 2,45		μC
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 150		1521 932		A/μs
Reverse recovered energy	E_{rec}					25 150		0,27 0,51		mWs
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,81		K/W

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Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_r [V] V_{CE} [V] V_{DS} [V]	I_C [A] I_F [A] I_D [A]	T_j [°C]	Min	Typ	Max	
Brake Switch										
Gate emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,00029	25	5	5,8	6,5	V
Collector-emitter saturation voltage	V_{CEsat}		15		20	25 150	1	1,58 1,76	2,2	V
Collector-emitter cut-off incl diode	I_{CES}		0	600		25			0,0011	mA
Gate-emitter leakage current	I_{GES}		20	0		25			300	nA
Integrated Gate resistor	R_{gint}							none		Ω
Turn-on delay time	$t_{d(on)}$					25 150		15 14		ns
Rise time	t_r					25 150		12 15		
Turn-off delay time	$t_{d(off)}$	R_{goff} = 8 Ω R_{gon} = 16 Ω	±15	300	20	25 150		197 220		
Fall time	t_f					25 150		100 119		
Turn-on energy loss	E_{on}					25 150		0,31 0,43		mWs
Turn-off energy loss	E_{off}					25 150		0,53 0,67		
Input capacitance	C_{ies}							1100		
Output capacitance	C_{oss}	f = 1 MHz	0	25		25		71		pF
Reverse transfer capacitance	C_{rss}							32		
Gate charge	Q_G		±15	480	20	25		120		nC
Thermal resistance junction to sink	$R_{th(j-s)}$	$λ_{paste}$ = 3,4 W/mK (PSX)						1,70		K/W
Brake Diode										
Diode forward voltage	V_F				20	25 150	1,25	1,83 1,76	1,95	V
Reverse leakage current	I_r			600		25			27	µA
Peak reverse recovery current	I_{RRM}					25 150		18 21		A
Reverse recovery time	t_{rr}					25 150		31 197		ns
Reverse recovered charge	Q_{rr}	R_{gon} = 16 Ω	±15	300	20	25 150		0,39 0,39		µC
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 150		1762 927		A/µs
Reverse recovery energy	E_{rec}					25 150		0,05 0,25		mWs
Thermal resistance junction to sink	$R_{th(j-s)}$	$λ_{paste}$ = 3,4 W/mK (PSX)						2,60		K/W
Thermistor										
Rated resistance	R					25		22000		Ω
Deviation of R_{100}	$Δ_{R/R}$	R_{100} = 1486 Ω				100	-5		5	%
Power dissipation	P					25		210		mW
Power dissipation constant						25		3,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±3%				25				K
B-value	$B_{(25/100)}$	Tol. ±3%				25		4000		K
Vincotech NTC Reference						25			A	

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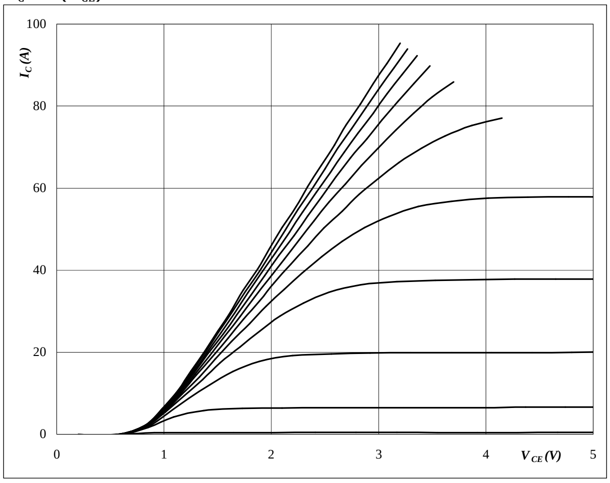
Inverter Characteristics

figure 1. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$



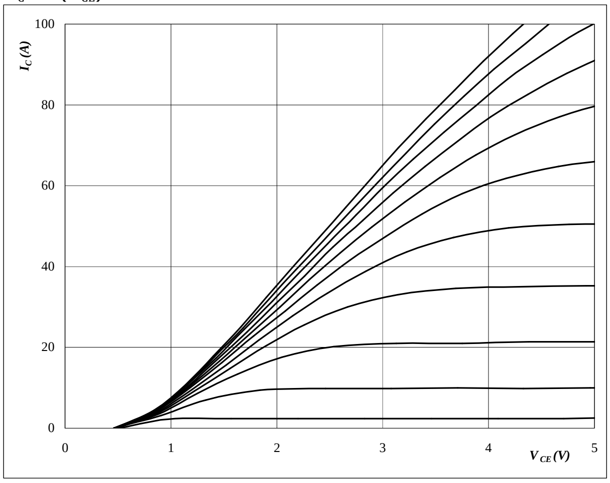
At

t_p =	250	µs
T_j =	25	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

figure 2. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$



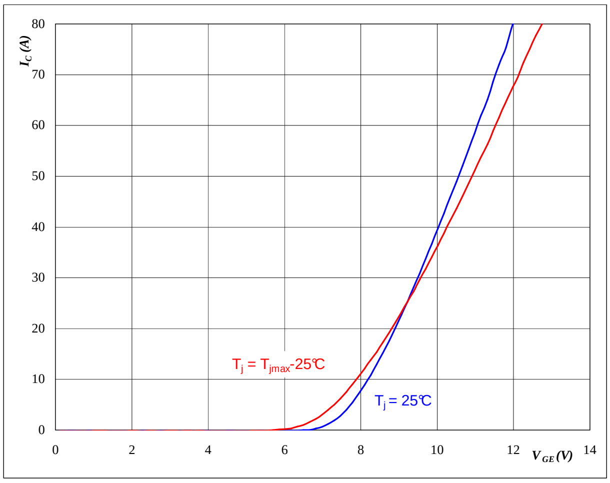
At

t_p =	250	µs
T_j =	125	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

figure 3. **IGBT**

Typical transfer characteristics

$I_C = f(V_{GE})$



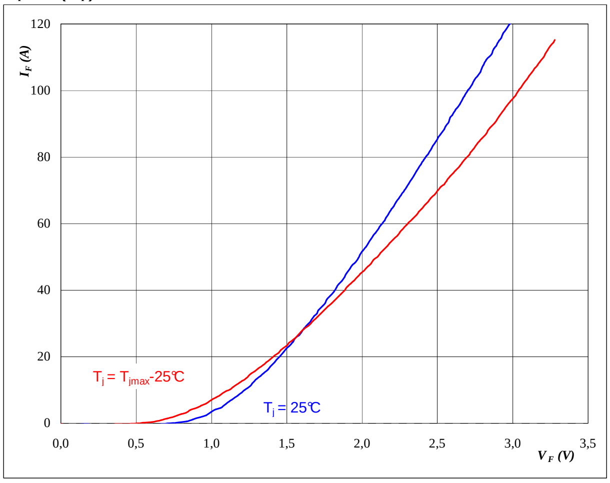
At

t_p =	250	µs
V_{CE} =	10	V

figure 4. **FWD**

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

t_p =	250	µs

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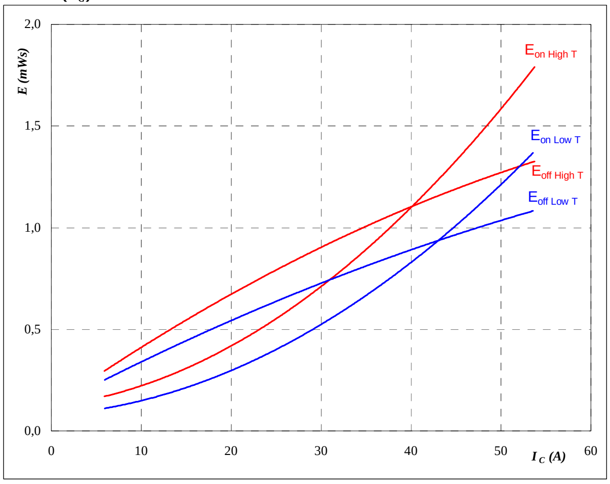
Inverter Characteristics

figure 5. **IGBT**

Typical switching energy losses
as a function of collector current

$E = f(I_C)$



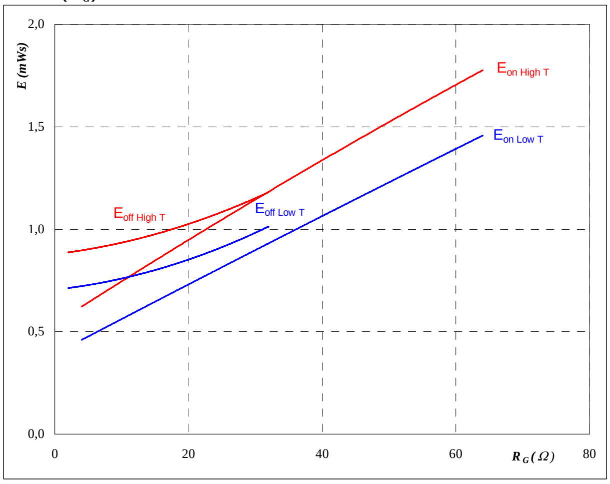
With an inductive load at

T_j =	25/125	°C
V_{CE} =	300	V
V_{GE} =	15	V
R_{gon} =	8	Ω
R_{goff} =	4	Ω

figure 6. **IGBT**

Typical switching energy losses
as a function of gate resistor

$E = f(R_G)$



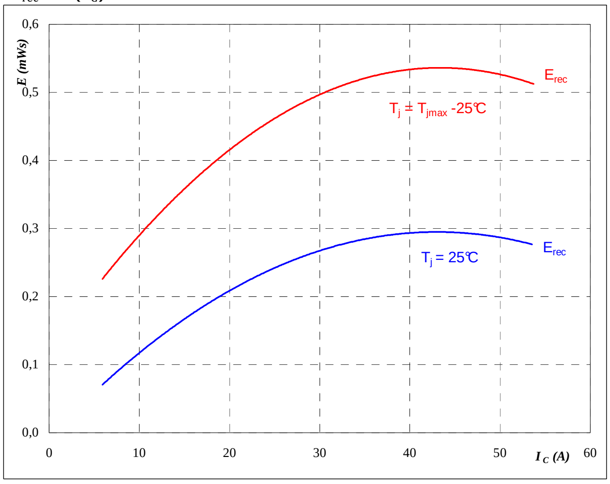
With an inductive load at

T_j =	25/125	°C
V_{CE} =	300	V
V_{GE} =	15	V
I_C =	30	A

figure 7. **FWD**

Typical reverse recovery energy loss
as a function of collector current

$E_{rec} = f(I_C)$



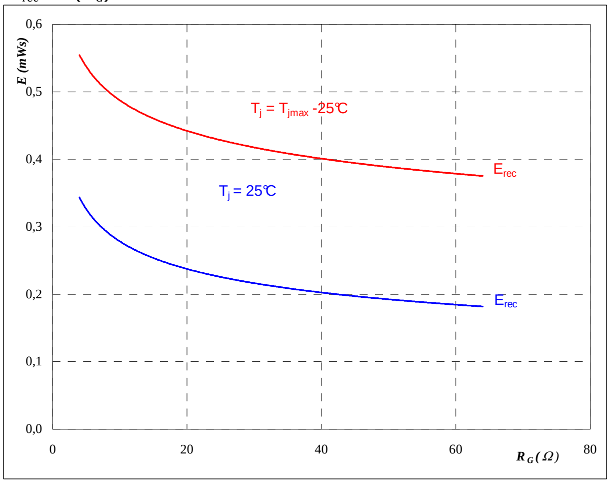
With an inductive load at

T_j =	25/125	°C
V_{CE} =	300	V
V_{GE} =	15	V
R_{gon} =	8	Ω

figure 8. **FWD**

Typical reverse recovery energy loss
as a function of gate resistor

$E_{rec} = f(R_G)$



With an inductive load at

T_j =	25/125	°C
V_{CE} =	300	V
V_{GE} =	15	V
I_C =	30	A

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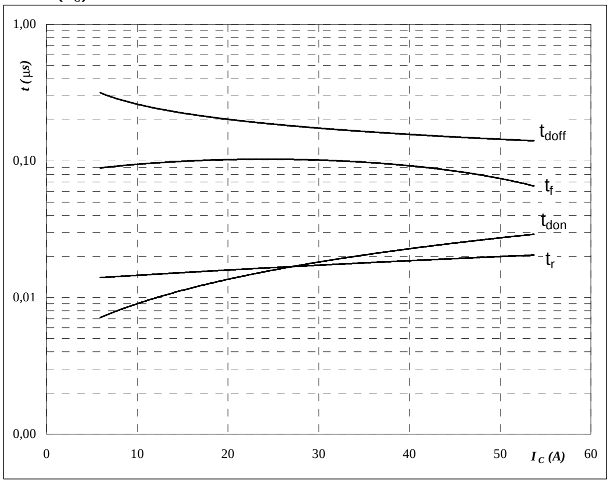
Inverter Characteristics

figure 9. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



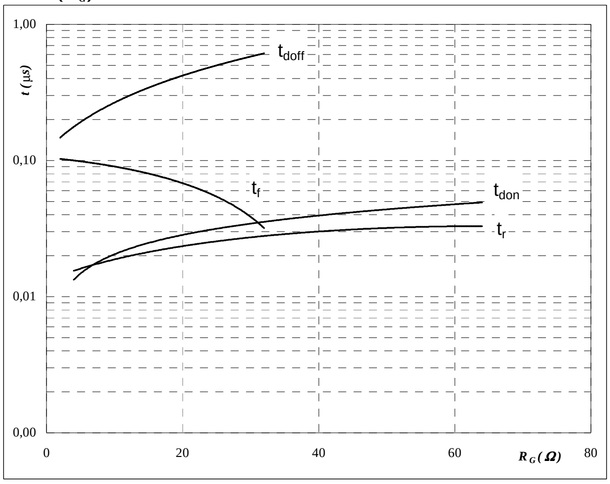
With an inductive load at

T_j =	125	°C
V_{CE} =	300	V
V_{GE} =	15	V
R_{gon} =	8	Ω
R_{goff} =	4	Ω

figure 10. **IGBT**

Typical switching times as a function of gate resistor

$t = f(R_G)$



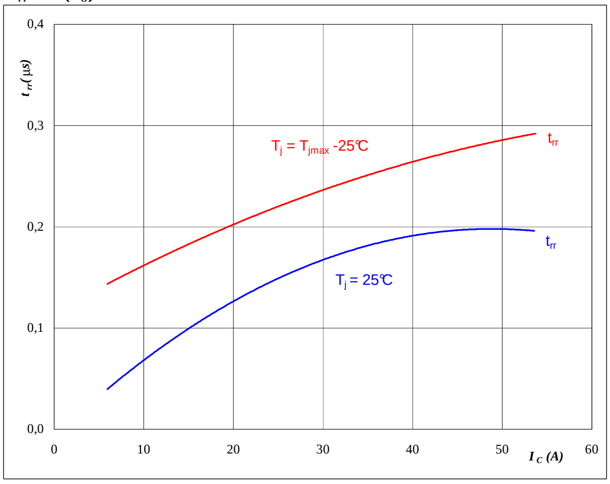
With an inductive load at

T_j =	125	°C
V_{CE} =	300	V
V_{GE} =	15	V
I_C =	30	A

figure 11. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$



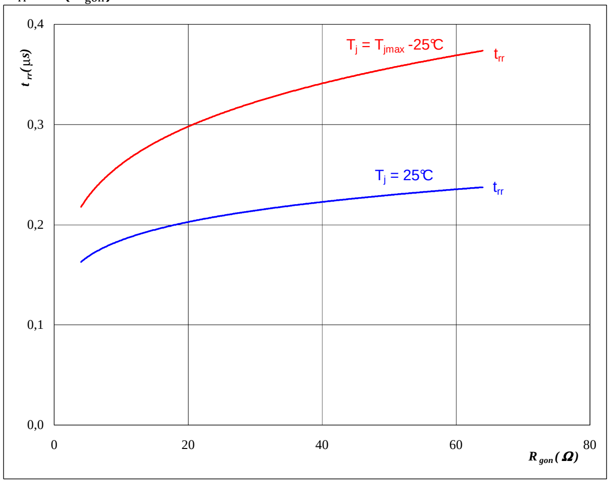
At

T_j =	25/125	°C
V_{CE} =	300	V
V_{GE} =	15	V
R_{gon} =	8	Ω

figure 12. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



At

T_j =	25/125	°C
V_R =	300	V
I_F =	30	A
V_{GE} =	15	V

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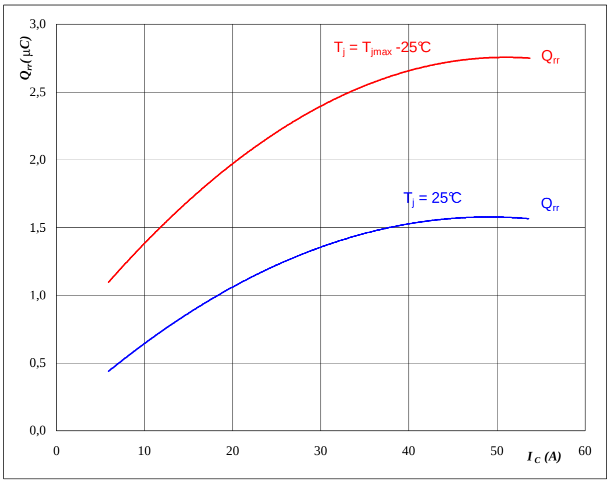
Inverter Characteristics

figure 13. **FWD**

Typical reverse recovery charge as a function of collector current

$Q_{rr} = f(I_C)$



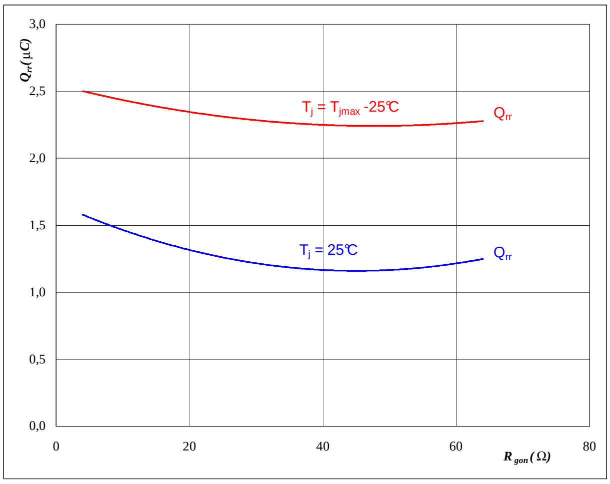
At

T_j =	25/125	°C
V_{CE} =	300	V
V_{GE} =	15	V
R_{gon} =	8	Ω

figure 14. **FWD**

Typical reverse recovery charge as a function of IGBT turn on gate resistor

$Q_{rr} = f(R_{gon})$



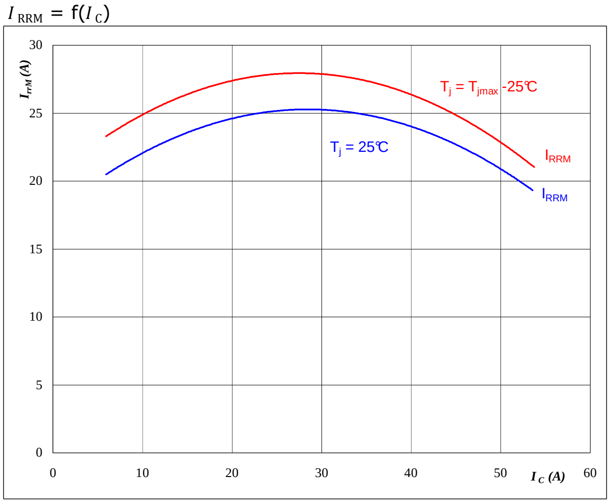
At

T_j =	25/125	°C
V_R =	300	V
I_F =	30	A
V_{GE} =	15	V

figure 15. **FWD**

Typical reverse recovery current as a function of collector current

$I_{RRM} = f(I_C)$



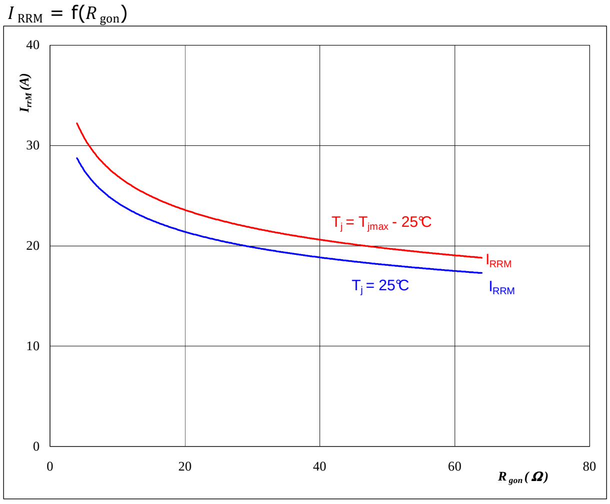
At

T_j =	25/125	°C
V_{CE} =	300	V
V_{GE} =	15	V
R_{gon} =	8	Ω

figure 16. **FWD**

Typical reverse recovery current as a function of IGBT turn on gate resistor

$I_{RRM} = f(R_{gon})$



At

T_j =	25/125	°C
V_R =	300	V
I_F =	30	A
V_{GE} =	15	V

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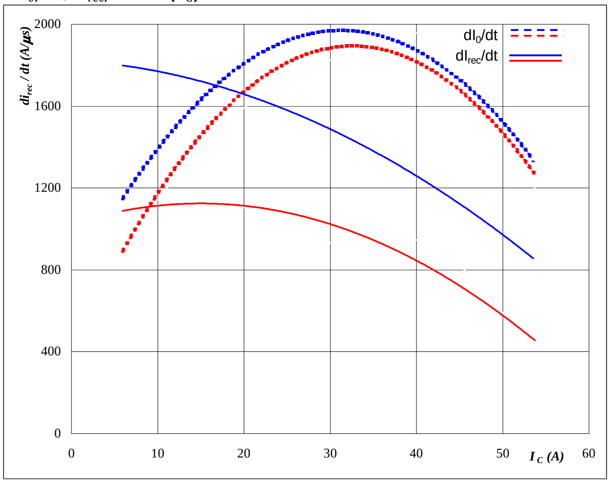
Inverter Characteristics

figure 17. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

$dI_0/dt, dI_{rec}/dt = f(I_C)$



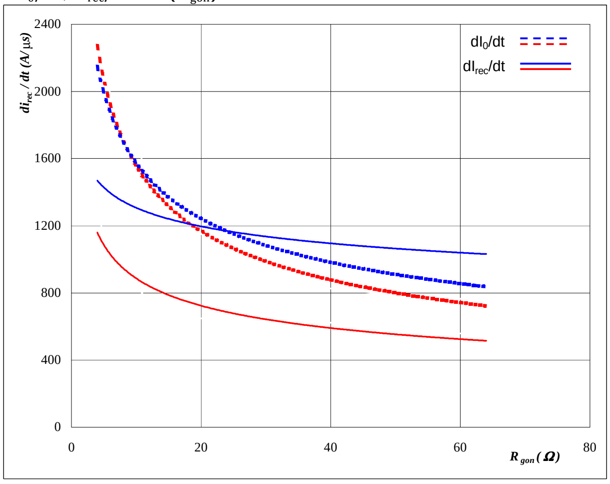
At

T_j =	25/125	°C
V_{CE} =	300	V
V_{GE} =	15	V
R_{gon} =	8	Ω

figure 18. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$dI_0/dt, dI_{rec}/dt = f(R_{gon})$



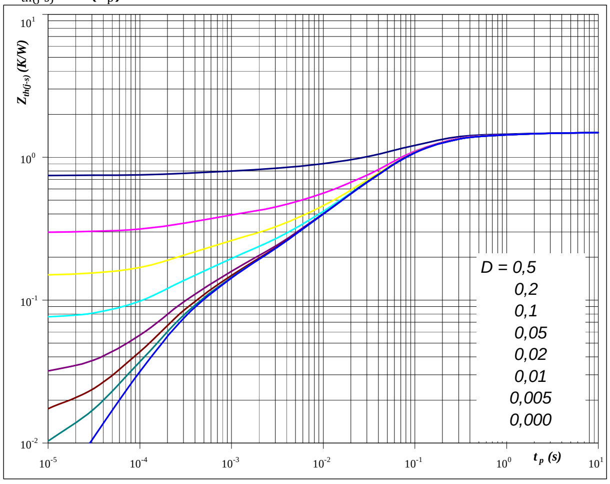
At

T_j =	25/125	°C
V_R =	300	V
I_F =	30	A
V_{GE} =	15	V

figure 19. **IGBT**

IGBT transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



At

D =	t_p / T	
$R_{th(j-s)}$ =	1,49	K/W

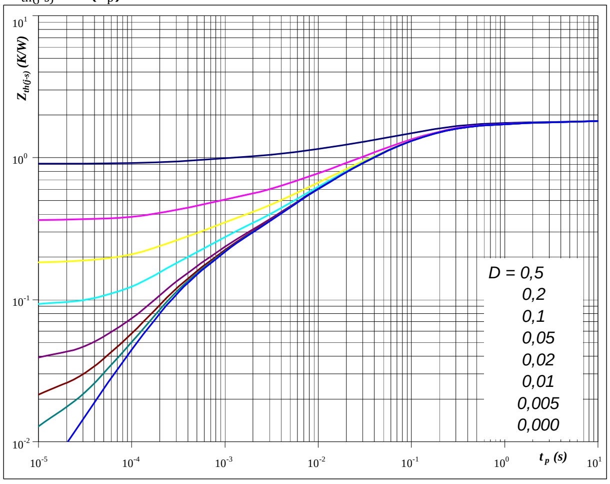
IGBT thermal model values

R (K/W)	Tau (s)
7,25E-02	2,02E+00
1,02E-01	4,53E-01
6,96E-01	8,91E-02
3,56E-01	3,19E-02
1,42E-01	5,59E-03
4,77E-02	9,74E-04
7,51E-02	2,56E-04

figure 20. **FWD**

FWD transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



At

D =	t_p / T	
$R_{th(j-s)}$ =	1,81	K/W

FWD thermal model values

R (K/W)	Tau (s)
8,32E-02	4,59E+00
2,00E-01	4,81E-01
7,57E-01	9,25E-02
4,20E-01	1,80E-02
2,12E-01	3,31E-03
1,39E-01	3,46E-04

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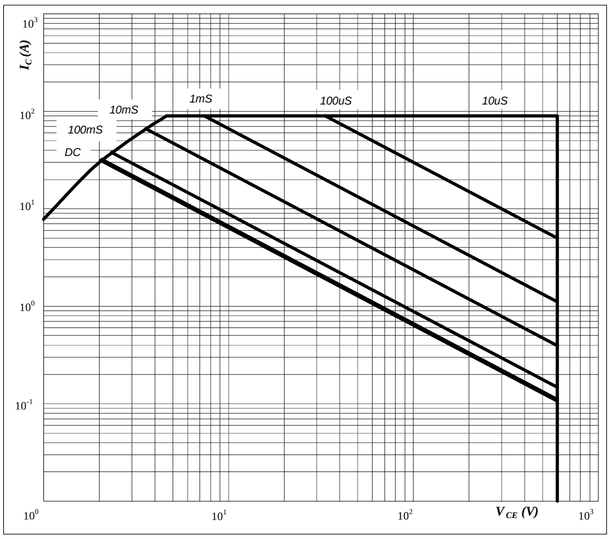
Inverter Characteristics

figure 25. **IGBT**

Safe operating area as a function of collector-emitter voltage

$I_C = f(V_{CE})$



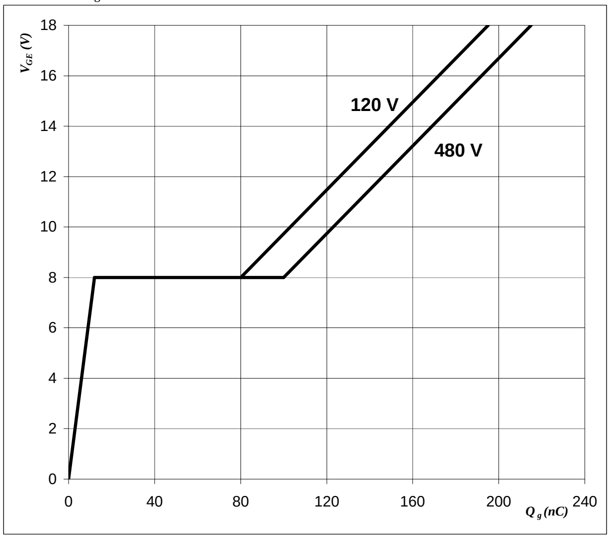
At

D =	single pulse	
T_s =	80	ºC
V_{GE} =	15	V
T_j =	T_{jmax}	

figure 26. **IGBT**

Gate voltage vs Gate charge

$V_{GE} = f(Q_g)$



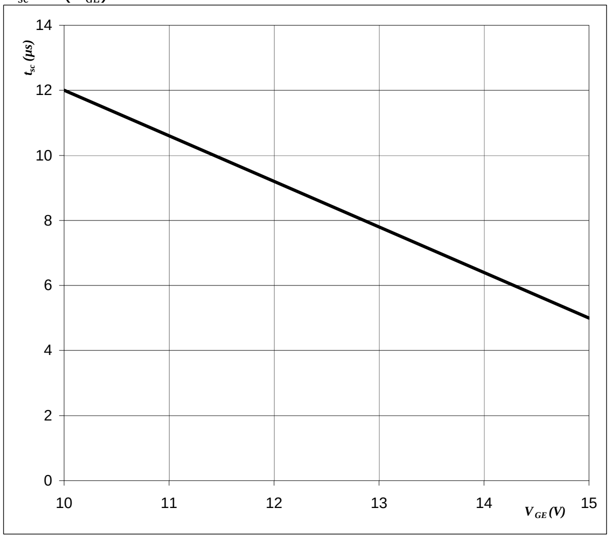
At

I_C =	30	A

figure 27. **IGBT**

Short circuit withstand time as a function of gate-emitter voltage

$t_{sc} = f(V_{GE})$



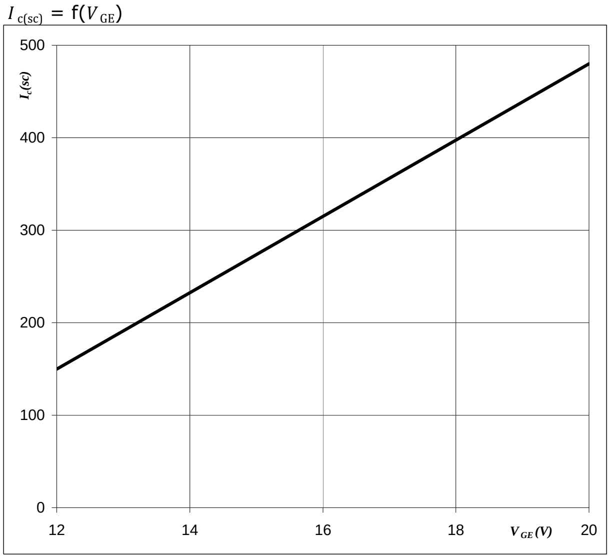
At

V_{CE} =	600	V
T_j ≤	175	ºC

figure 28. **IGBT**

Typical short circuit collector current as a function of gate-emitter voltage

$I_{c(sc)} = f(V_{GE})$



At

V_{CE} ≤	600	V
T_j =	175	ºC

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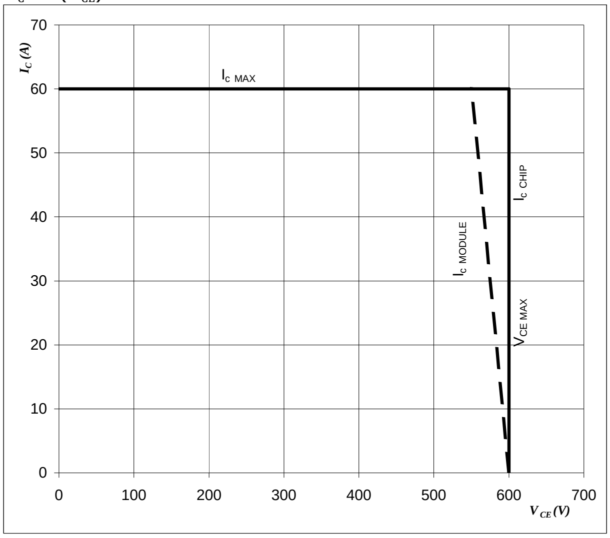
figure 29. **IGBT**

Reverse bias safe operating area

$I_C = f(V_{CE})$



At

T_j = T_{jmax}-25 ºC

Switching mode : 3phase SPWM

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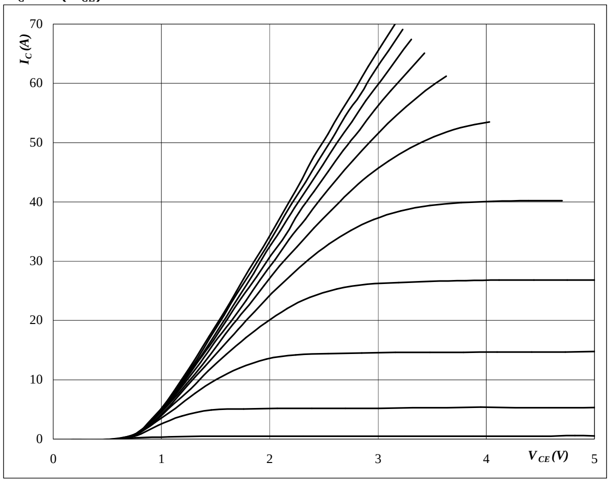
Brake Characteristics

figure 1. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$



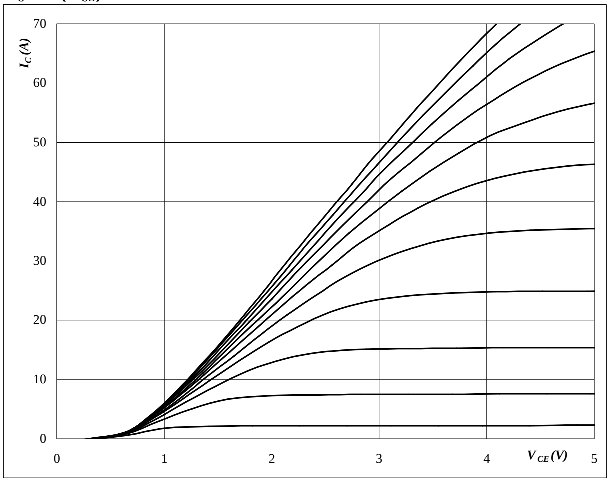
At

t_p =	250	μs
T_j =	25	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

figure 2. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$



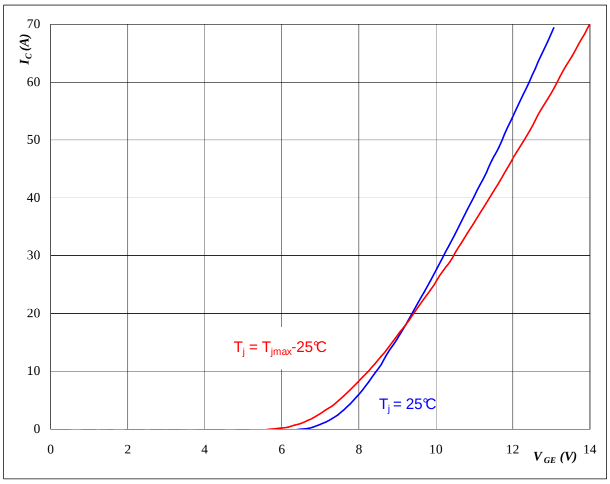
At

t_p =	250	μs
T_j =	125	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

figure 3. **IGBT**

Typical transfer characteristics

$I_C = f(V_{GE})$



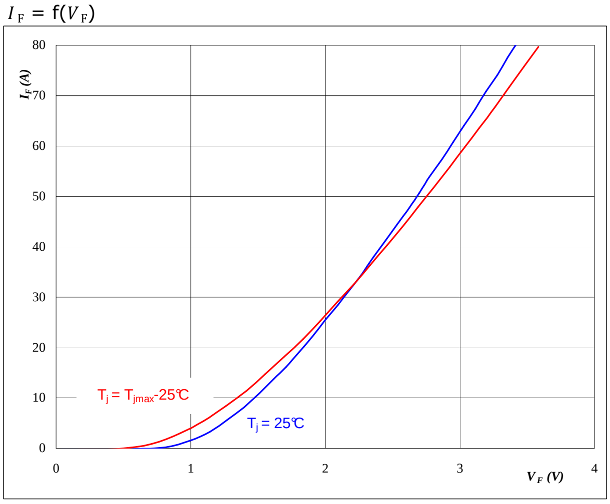
At

t_p =	250	μs
V_{CE} =	10	V

figure 4. **FWD**

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



At

t_p =	250	μs

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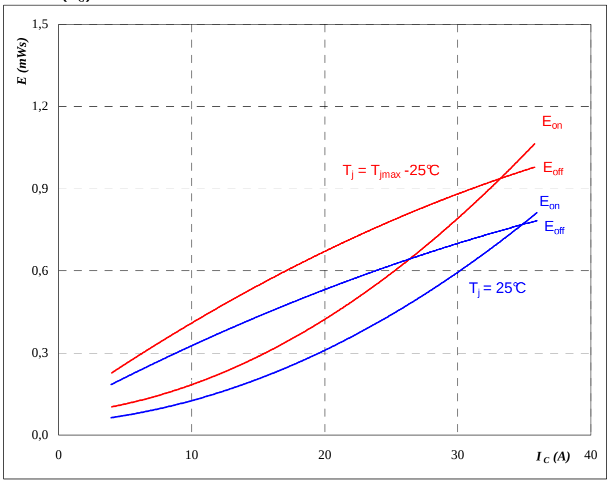
Brake Characteristics

figure 5.	IGBT

Typical switching energy losses
as a function of collector current

$E = f(I_C)$



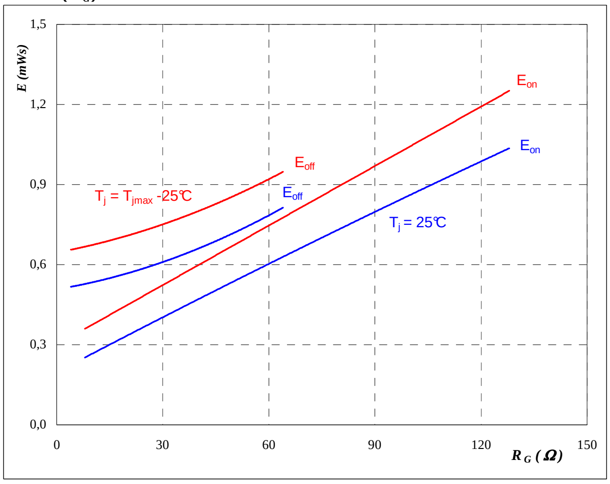
With an inductive load at

T_j =	25/125	°C
V_{CE} =	300	V
V_{GE} =	15	V
R_{gon} =	16	Ω
R_{goff} =	8	Ω

figure 6.	IGBT

Typical switching energy losses
as a function of gate resistor

$E = f(R_G)$



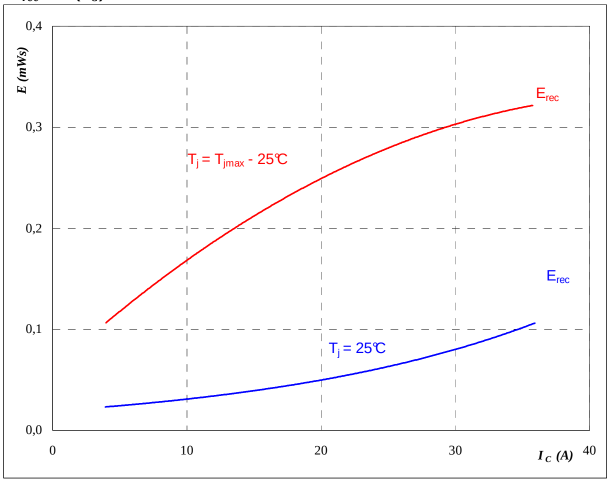
With an inductive load at

T_j =	25/125	°C
V_{CE} =	300	V
V_{GE} =	15	V
I_C =	20	A

figure 7.	FWD

Typical reverse recovery energy loss
as a function of collector current

$E_{rec} = f(I_C)$



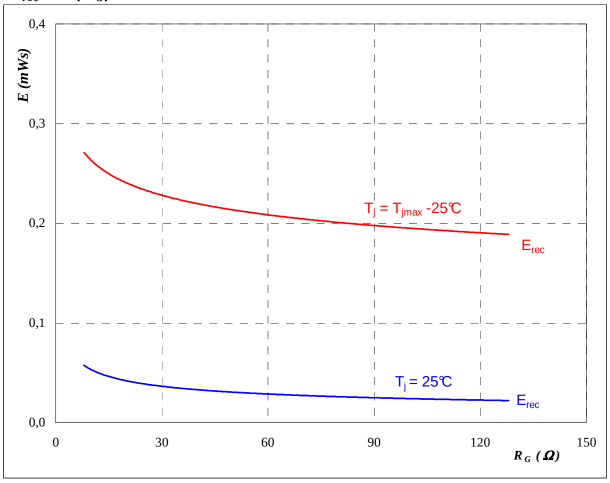
With an inductive load at

T_j =	25/125	°C
V_{CE} =	300	V
V_{GE} =	15	V
R_{gon} =	16	Ω

figure 8.	FWD

Typical reverse recovery energy loss
as a function of gate resistor

$E_{rec} = f(R_G)$



With an inductive load at

T_j =	25/125	°C
V_{CE} =	300	V
V_{GE} =	15	V
I_C =	20	A

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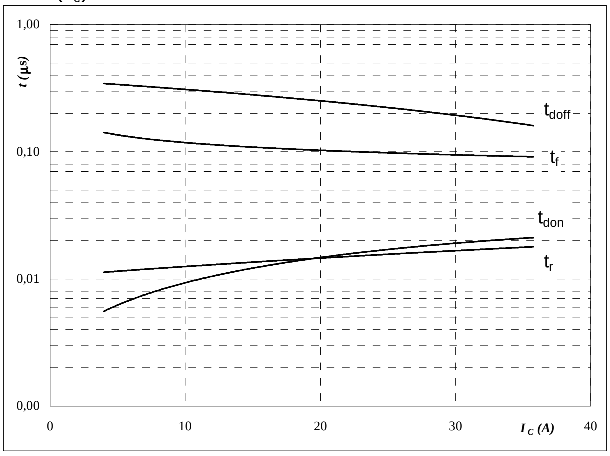
Brake Characteristics

figure 9. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



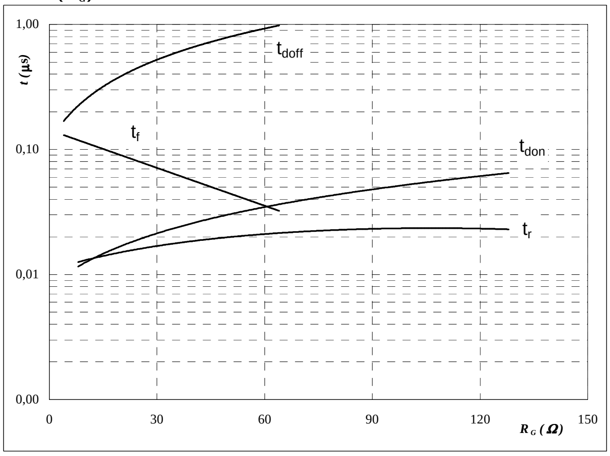
With an inductive load at

T_j =	25/125	°C
V_{CE} =	300	V
V_{GE} =	15	V
R_{gon} =	16	Ω
R_{goff} =	8	Ω

figure 10. **IGBT**

Typical switching times as a function of gate resistor

$t = f(R_G)$



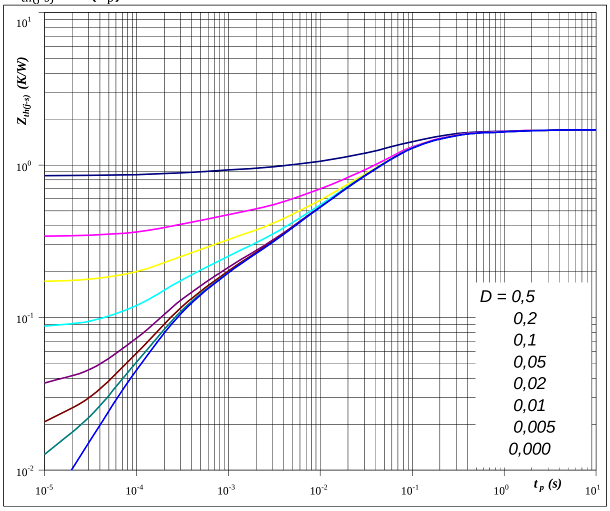
With an inductive load at

T_j =	25/125	°C
V_{CE} =	300	V
V_{GE} =	15	V
I_C =	20	A

figure 11. **IGBT**

IGBT transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



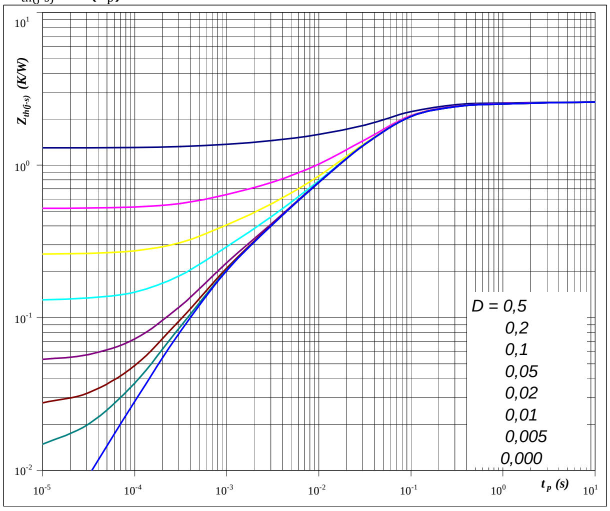
At

D =	t_p / T	
$R_{th(j-s)}$ =	1,70	K/W

figure 12. **FWD**

FWD transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



At

D =	t_p / T	
$R_{th(j-s)}$ =	2,60	K/W

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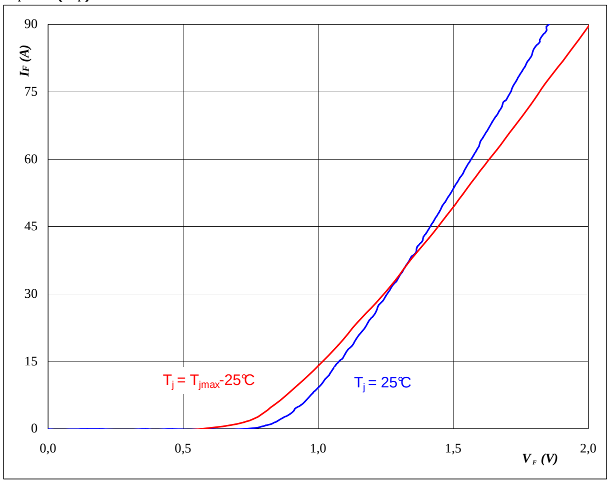
Rectifier Diode

figure 1.	**Rectifier Diode**

Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



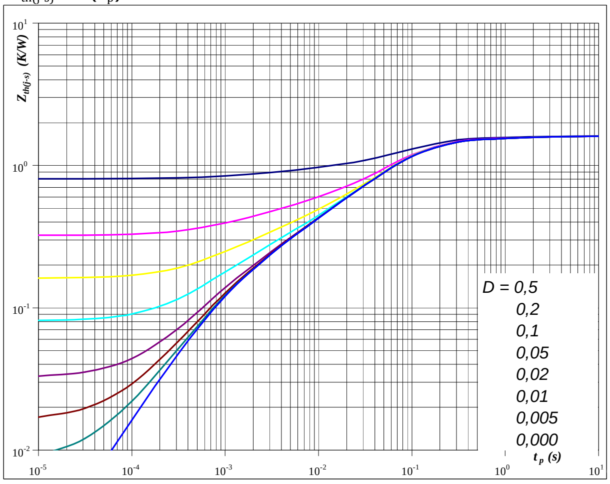
At

t_p = 250 µs

figure 2.	**Rectifier Diode**

Diode transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



At

$D = t_p / T$

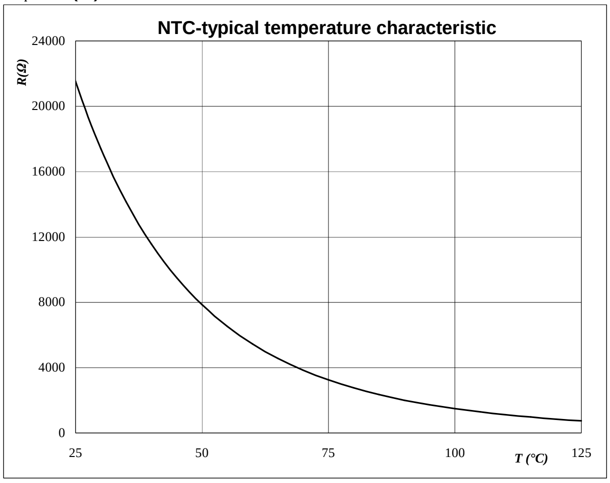
$R_{th(j-s)}$ = 1,61 K/W

Thermistor

figure 1.	**Thermistor**

Typical NTC characteristic as a function of temperature

$R_T = f(T)$



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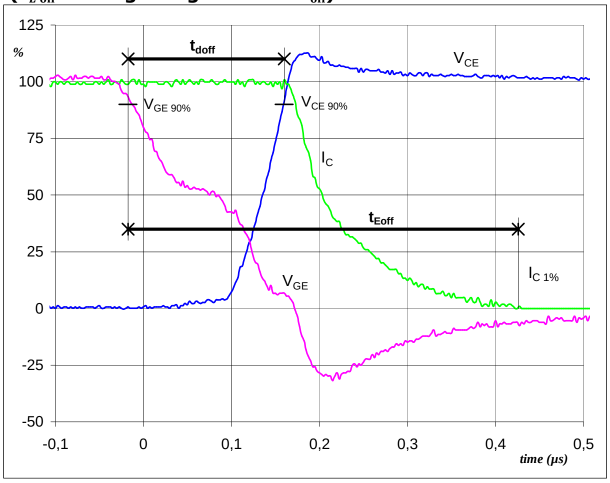
Switching Definitions Inverter

General conditions

T_j	=	125 °C
R_{gon}	=	8 Ω
R_{goff}	=	4 Ω

figure 1. **IGBT**

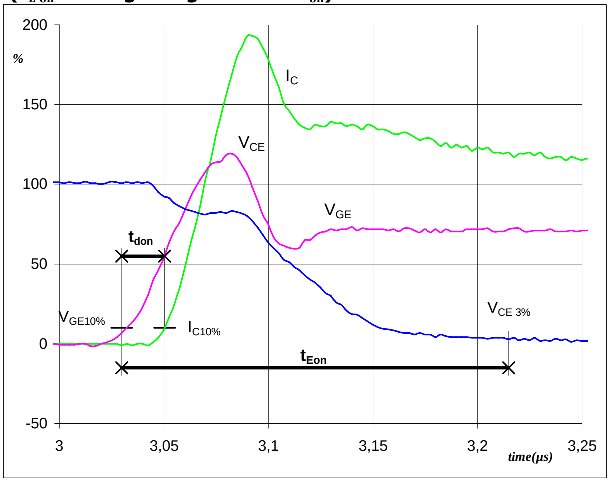
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff}
($t_{E\,off}$ = integrating time for E_{off})



V_{GE} (0%) =	0	V	
V_{GE} (100%) =	15	V	
V_C (100%) =	300	V	
I_C (100%) =	30	A	µ
t_{doff} =	0,17	µs	
$t_{E\,off}$ =	0,44	µs	

figure 2. **IGBT**

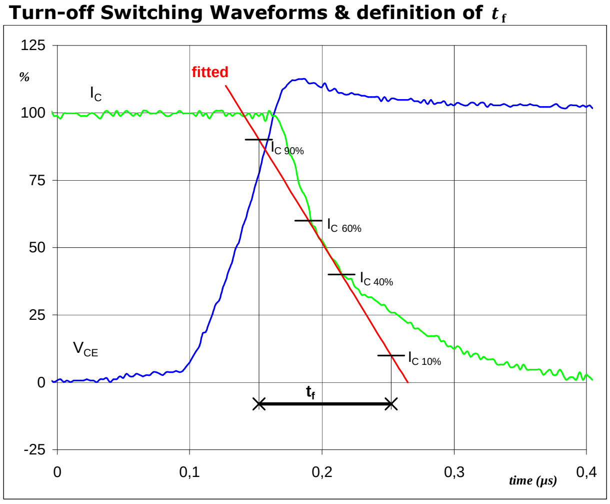
Turn-on Switching Waveforms & definition of t_{don}, t_{Eon}
($t_{E\,on}$ = integrating time for E_{on})



V_{GE} (0%) =	0	V
V_{GE} (100%) =	15	V
V_C (100%) =	300	V
I_C (100%) =	30	A
t_{don} =	0,02	µs
$t_{E\,on}$ =	0,18	µs

figure 3. **IGBT**

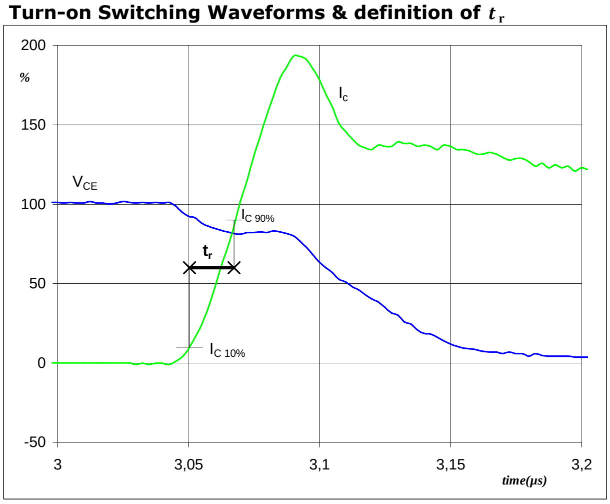
Turn-off Switching Waveforms & definition of t_f



V_C (100%) =	300	V
I_C (100%) =	30	A
t_f =	0,10	µs

figure 4. **IGBT**

Turn-on Switching Waveforms & definition of t_r



V_C (100%) =	300	V
I_C (100%) =	30	A
t_r =	0,02	µs

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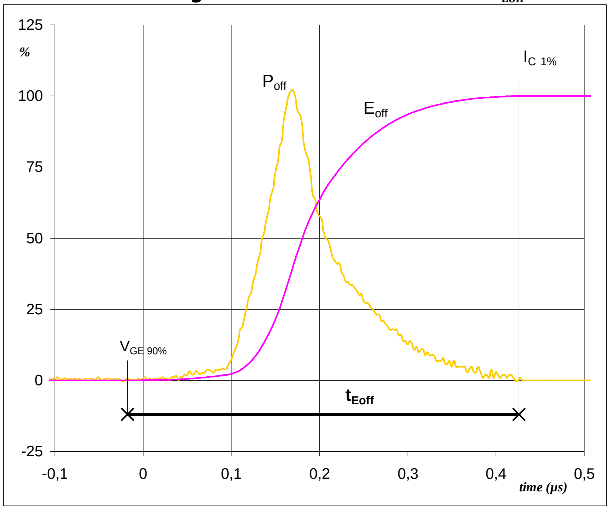
Switching Definitions Inverter

figure 5. **IGBT**

Turn-off Switching Waveforms & definition of t_{Eoff}



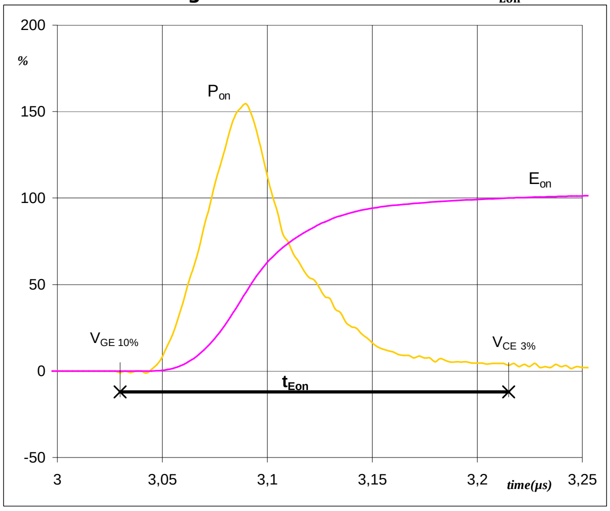
P_{off} (100%) = 8,98 kW

E_{off} (100%) = 0,90 mJ

$t_{E\,off}$ = 0,44 µs

figure 6. **IGBT**

Turn-on Switching Waveforms & definition of t_{Eon}



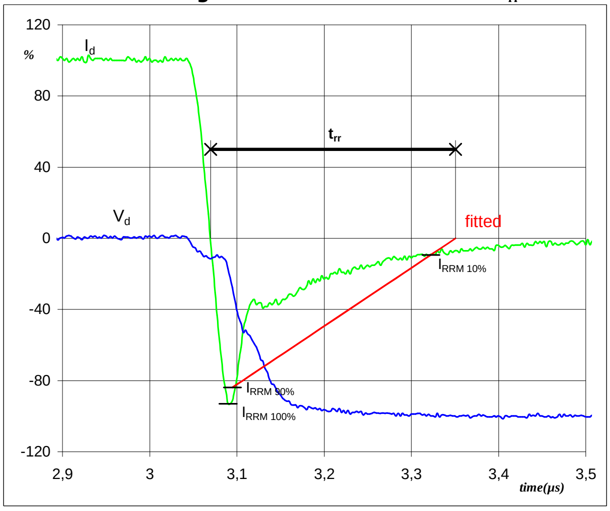
P_{on} (100%) = 8,98 kW

E_{on} (100%) = 0,71 mJ

$t_{E\,on}$ = 0,18 µs

figure 7. **IGBT**

Turn-off Switching Waveforms & definition of t_{rr}



V_d (100%) = 300 V

I_d (100%) = 30 A

I_{RRM} (100%) = 28 A

t_{rr} = 0,26 µs

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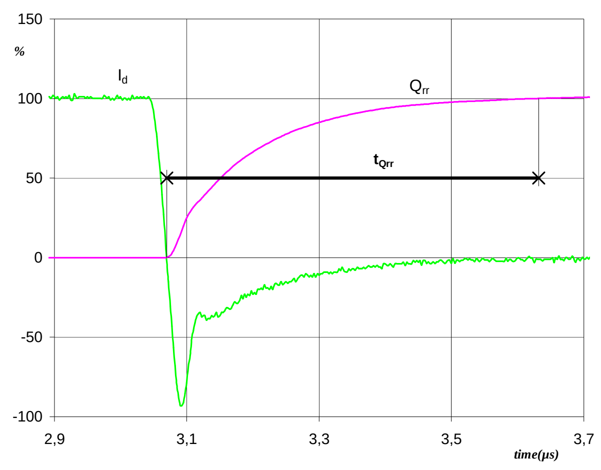
Switching Definitions Inverter

figure 8. **FWD**

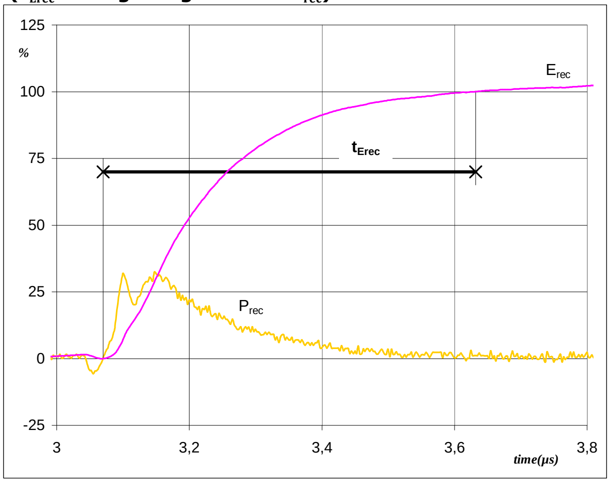
Turn-on Switching Waveforms & definition of t_{Qrr}
($t_{Q\,rr}$ = integrating time for Q_{rr})



I_d (100%) =	30	A
Q_{rr} (100%) =	2,45	µC
$t_{Q\,rr}$ =	0,56	µs

figure 9. **FWD**

Turn-on Switching Waveforms & definition of t_{Erec}
(t_{Erec}= integrating time for E_{rec})



P_{rec} (100%) =	8,98	kW
E_{rec} (100%) =	0,51	mJ
$t_{E\,rec}$ =	0,56	µs

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Ordering Code and Marking - Outline - Pinout

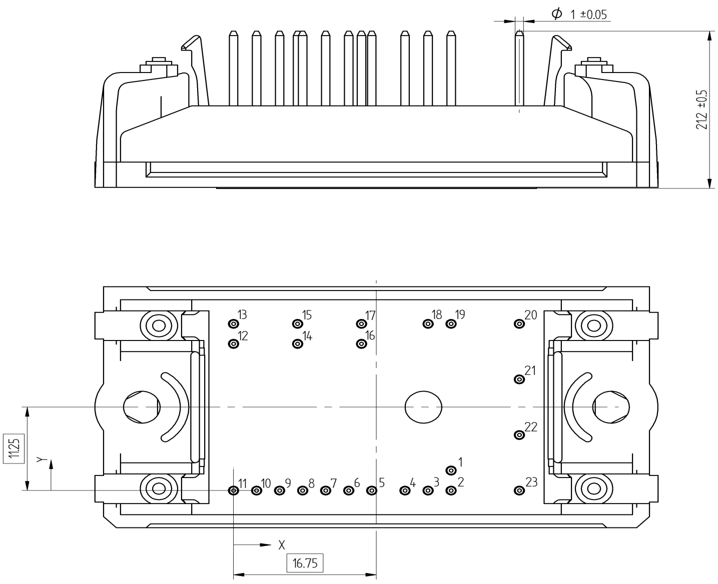
Ordering Code & Marking

Version	Ordering Code
without thermal paste 17mm housing with solder pins	V23990-P546-A20-PM

Text	VIN	Date code	Name&Ver	UL	Lot	Serial
	VIN	WWYY	NNNNNNNNVV	UL	LLLLL	SSSS
Datamatrix	Name&Ver	Lot number	Serial	Date code		
	NNNNNNNNVV	LLLLL	SSSS	WWYY		

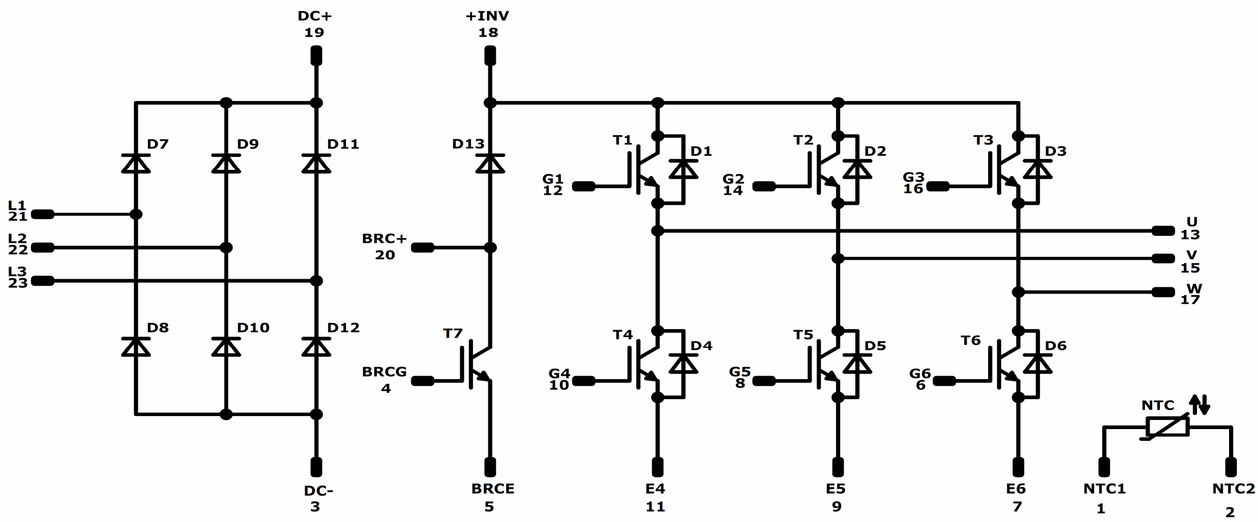
Outline

Pin table			
Pin	X	Y	Function
1	25,5	2,7	NTC1
2	25,5	0	NTC2
3	22,8	0	-DC
4	20,1	0	BRCG
5	16,2	0	BRCE
6	13,5	0	G6
7	10,8	0	E6
8	8,1	0	G5
9	5,4	0	E5
10	2,7	0	G4
11	0	0	E4
12	0	19,8	G1
13	0	22,5	U
14	7,5	19,8	G2
15	7,5	22,5	V
16	15	19,8	G3
17	15	22,5	W
18	22,8	22,5	+INV
19	25,5	22,5	+DC
20	33,5	22,5	BRC+
21	33,5	15	L1
22	33,5	7,5	L2
23	33,5	0	L3



Tolerance of pinpositions: ±0,5mm at the end of pins
Dimension of coordinate axis is only offset without tolerance

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T1-T6	IGBT	600V	30A	Inverter Switch	
D1-D6	FWD	600V	30A	Inverter Diode	
T7	IGBT	600V	20A	Brake Switch	
D13	FWD	600V	20A	Brake Diode	
D7-D12	FWD	1600V	25A	Rectifier Diode	
NTC	NTC			Thermistor	

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Packaging instruction					
Standard packaging quantity (SPQ)	**135**	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 0 packages see vincotech.com website.

Package data
Package data for *flow* 0 packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
V23990-P546-A20-D6-14	15 Apr. 2019	R_{th}, I_{max}, P_{tot} celarance values corrected	All

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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